

$V_{DSS}$	30V
$R_{DS(on)}(Max.)$	27mΩ
$I_D$	±7A
$P_D$	2W

### ●Features

- 1) Low on - resistance.
- 2) High Power Package (HSMT8).
- 3) Pb-free lead plating ; RoHS compliant.
- 4) Halogen Free.

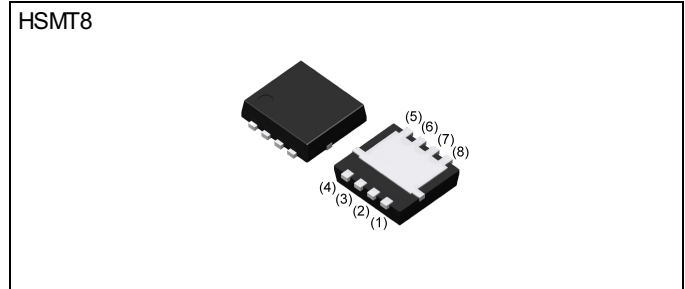
### ●Application

Switching

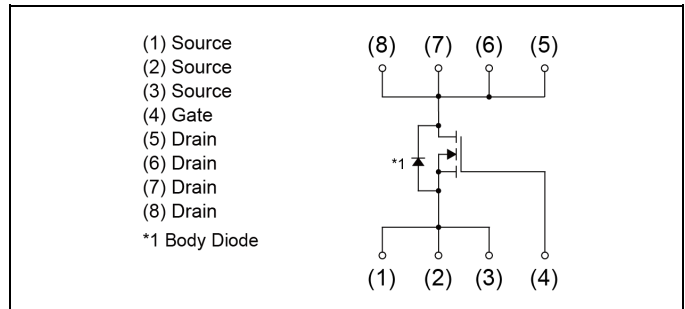
### ●Absolute maximum ratings ( $T_a = 25^{\circ}C$ )

Parameter	Symbol	Value	Unit
Drain - Source voltage	$V_{DSS}$	30	V
Continuous drain current	$I_D$	±7	A
Pulsed drain current	$I_{D,pulse}^{*1}$	±28	A
Gate - Source voltage	$V_{GSS}$	±20	V
Power dissipation	$P_D^{*2}$	2	W
Junction temperature	$T_j$	150	°C
Range of storage temperature	$T_{stg}$	-55 to +150	°C

### ●Outline



### ●Inner circuit



### ●Packaging specifications

Type	Packing	Embossed Tape
	Reel size (mm)	330
	Tape width (mm)	12
	Basic ordering unit (pcs)	3000
	Taping code	TB
	Marking	E070BN

### ● Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - ambient	$R_{thJA}^{*2}$	-	62.5	-	°C/W

### ● Electrical characteristics ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 1mA$	30	-	-	V
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_j}$	$I_D = 1mA$ referenced to $25^\circ\text{C}$	-	21	-	mV/°C
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 30V, V_{GS} = 0V$	-	-	1	μA
Gate - Source leakage current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	±100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = 10V, I_D = 1mA$	1.0	-	2.5	V
Gate threshold voltage temperature coefficient	$\frac{\Delta V_{GS(th)}}{\Delta T_j}$	$I_D = 1mA$ referenced to $25^\circ\text{C}$	-	-3	-	mV/°C
Static drain - source on - state resistance	$R_{DS(on)}^{*3}$	$V_{GS} = 10V, I_D = 7A$	-	20	27	mΩ
		$V_{GS} = 4.5V, I_D = 7A$	-	29	39	
Gate input resistance	$R_G$		-	3.3	-	Ω
Transconductance	$g_{fs}^{*3}$	$V_{DS} = 5V, I_D = 7A$	4	-	-	S

\*1  $P_w \leq 10\mu\text{s}$ , Duty cycle  $\leq 1\%$

\*2 Mounted on a ceramic board (30×30×0.8mm)

\*3 Pulsed

**● Electrical characteristics** ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	$C_{iss}$	$V_{GS} = 0V$	-	410	-	pF
Output capacitance	$C_{oss}$	$V_{DS} = 15V$	-	50	-	
Reverse transfer capacitance	$C_{rss}$	$f = 1\text{MHz}$	-	40	-	
Turn - on delay time	$t_{d(on)}^{*3}$	$V_{DD} \approx 15V, V_{GS} = 10V$	-	6	-	ns
Rise time	$t_r^{*3}$	$I_D = 3.5A$	-	8	-	
Turn - off delay time	$t_{d(off)}^{*3}$	$R_L = 4.29\Omega$	-	23	-	
Fall time	$t_f^{*3}$	$R_G = 10\Omega$	-	5	-	

**● Gate charge characteristics** ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Conditions		Values			Unit
				Min.	Typ.	Max.	
Total gate charge	$Q_g^{*3}$	$V_{DD} \approx 15V$ $I_D = 7A$	$V_{GS} = 10V$	-	8.9	-	nC
Gate - Source charge	$Q_{gs}^{*3}$		$V_{GS} = 4.5V$	-	4.6	-	
Gate - Drain charge	$Q_{gd}^{*3}$		$V_{GS} = 4.5V$	-	1.9	-	
				-	1.4	-	

**● Body diode electrical characteristics** (Source-Drain) ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Body diode continuous forward current	$I_S$	$T_a = 25^\circ\text{C}$	-	-	1.67	A
Body diode pulse current	$I_{SP}^{*1}$		-	-	28	
Forward voltage	$V_{SD}^{*3}$	$V_{GS} = 0V, I_S = 1.67A$	-	-	1.2	V

● Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve



Fig.2 Maximum Safe Operating Area

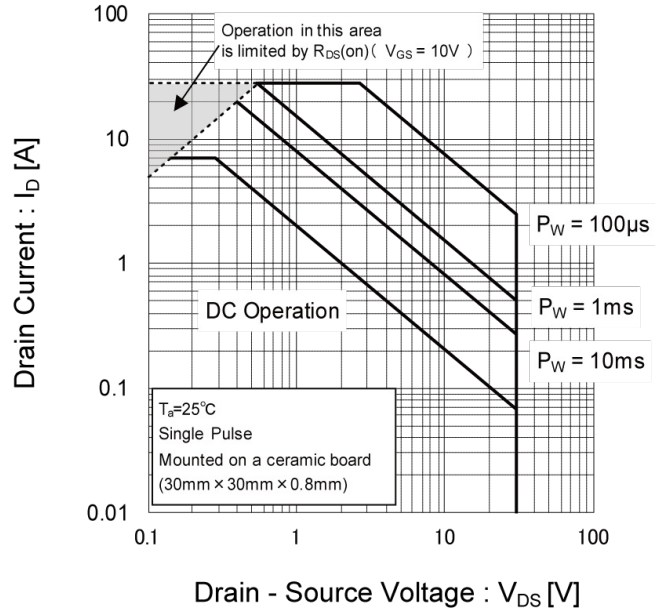


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

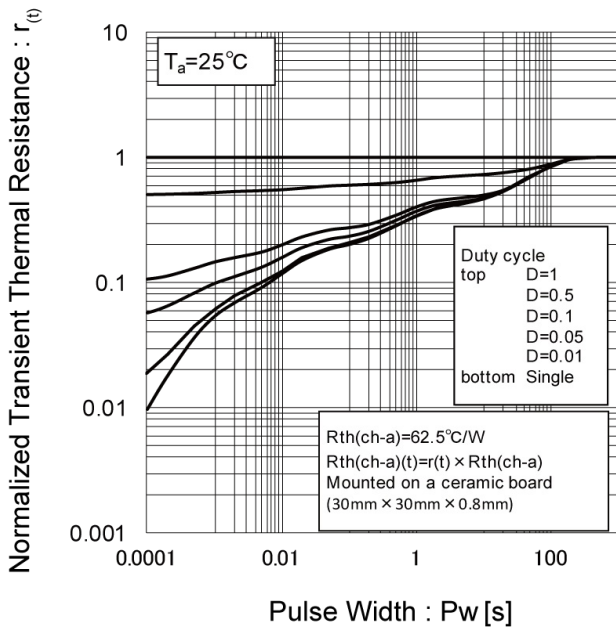
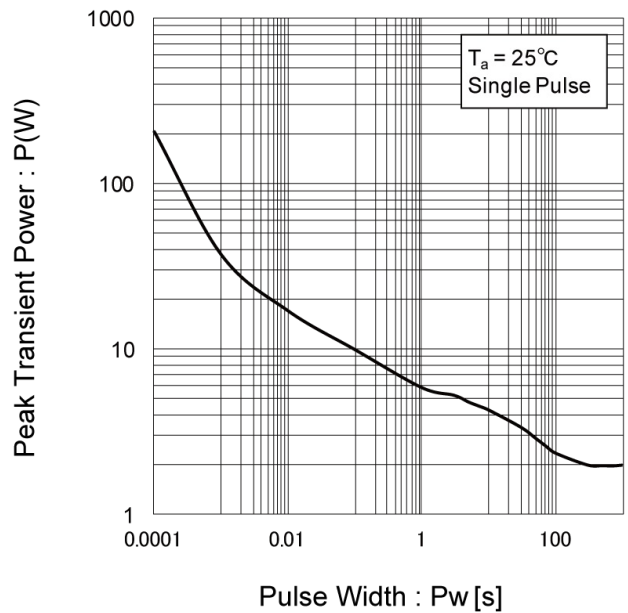


Fig.4 Single Pulse Maximum Power dissipation



● Electrical characteristic curves

Fig.5 Typical Output Characteristics(I)

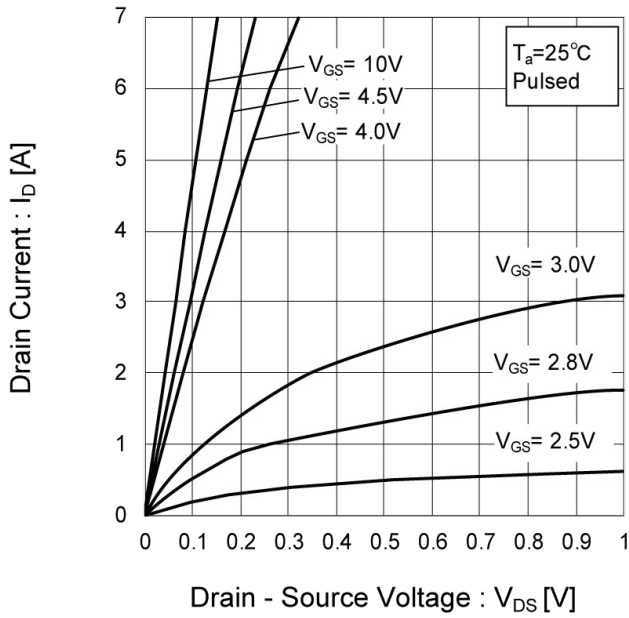


Fig.6 Typical Output Characteristics(II)

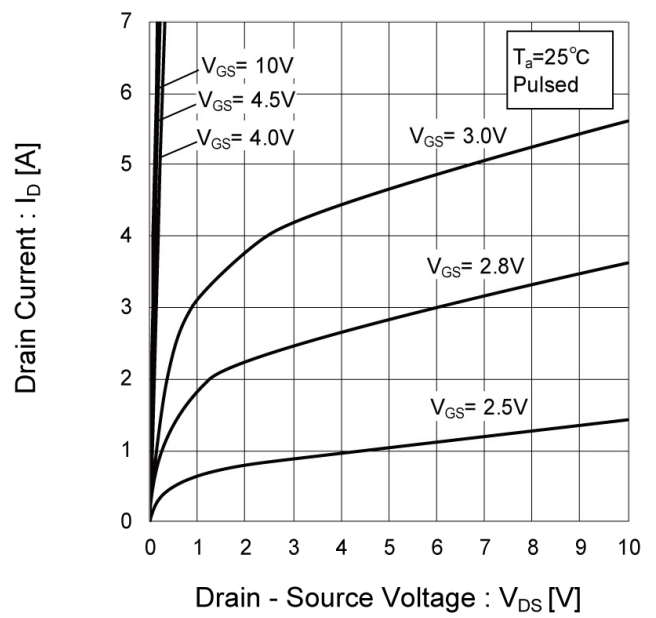
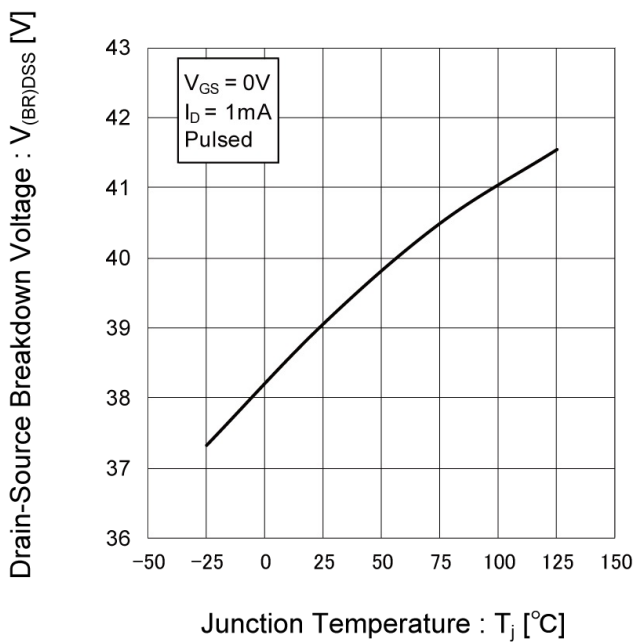


Fig.7 Breakdown Voltage vs. Junction Temperature



●Electrical characteristic curves

Fig.8 Typical Transfer Characteristics

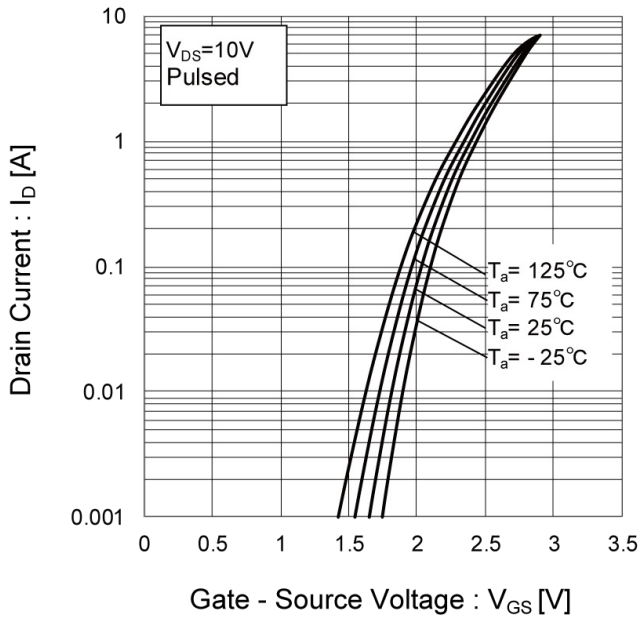


Fig.9 Gate Threshold Voltage vs. Junction Temperature

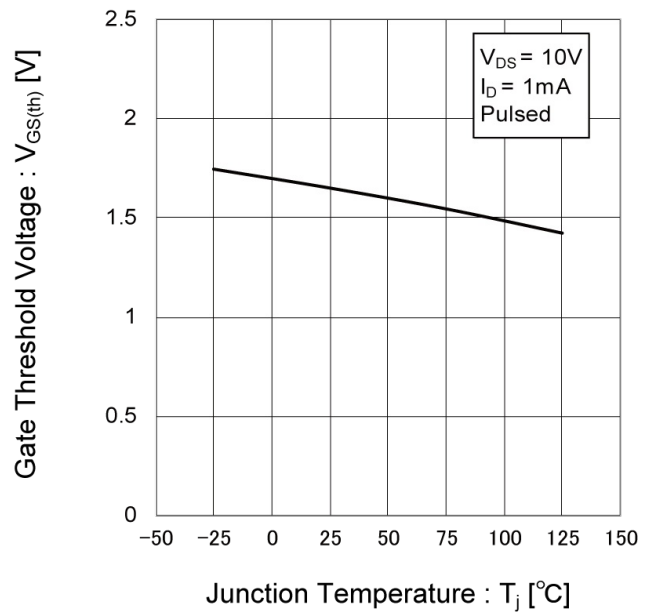
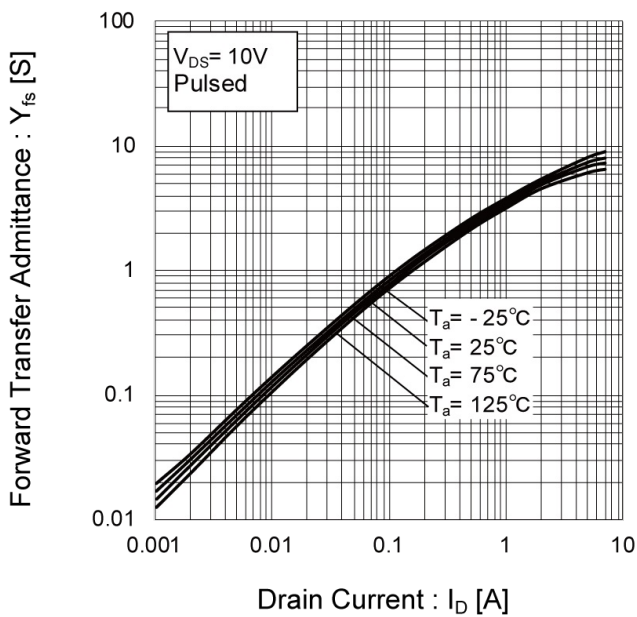


Fig.10 Transconductance vs. Drain Current



● Electrical characteristic curves

Fig.11 Drain Current Derating Curve

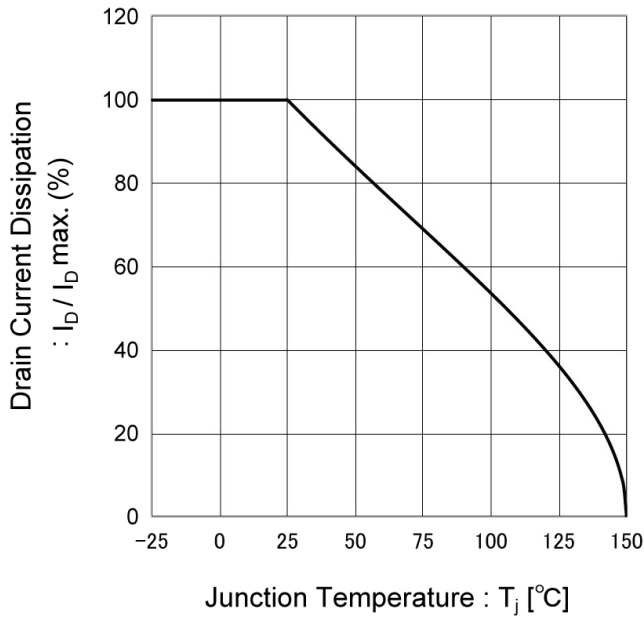


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

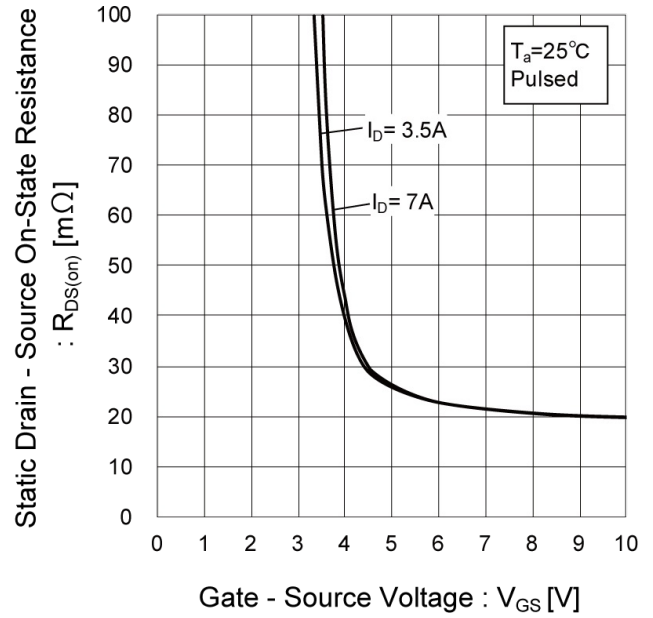
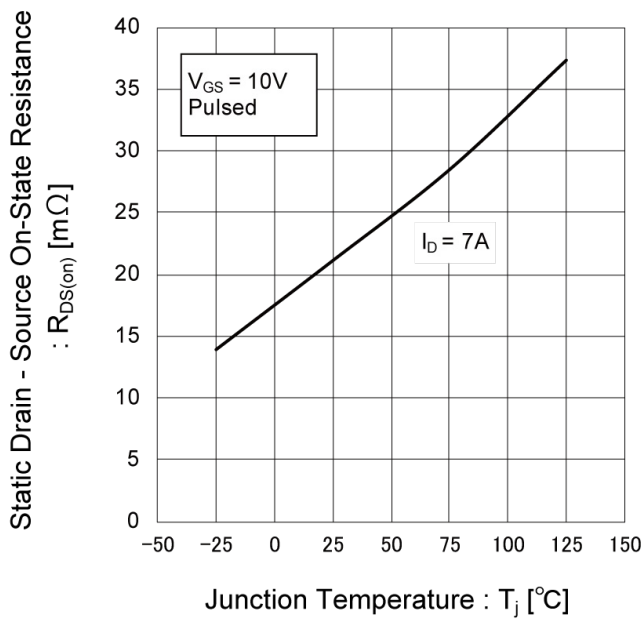


Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature



● Electrical characteristic curves

Fig.14 Static Drain - Source On - State Resistance vs. Drain Current(I)

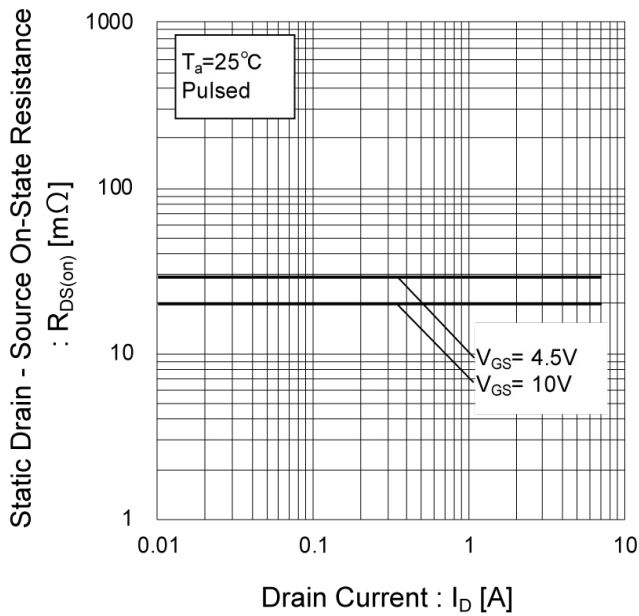


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(II)

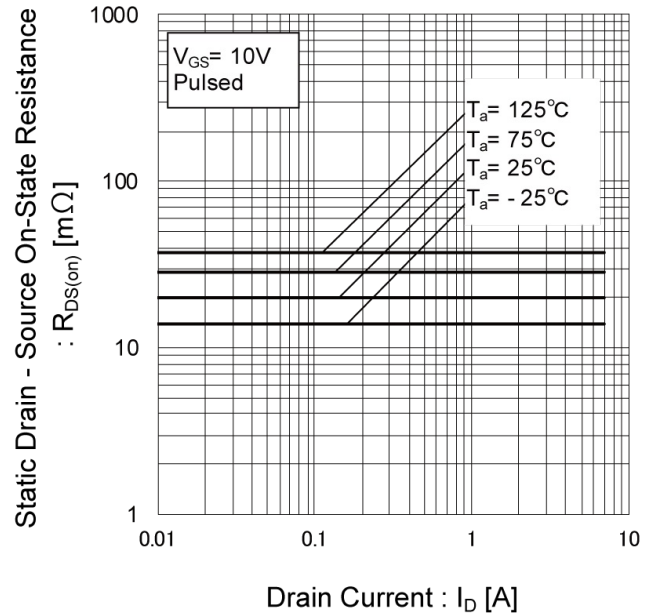
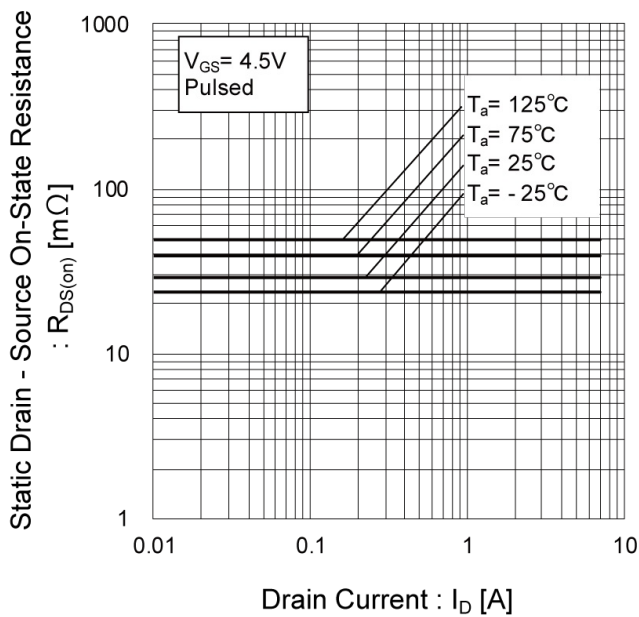


Fig.16 Static Drain - Source On - State Resistance vs. Drain Current(III)





● Electrical characteristic curves

Fig.17 Typical Capacitance vs. Drain - Source Voltage

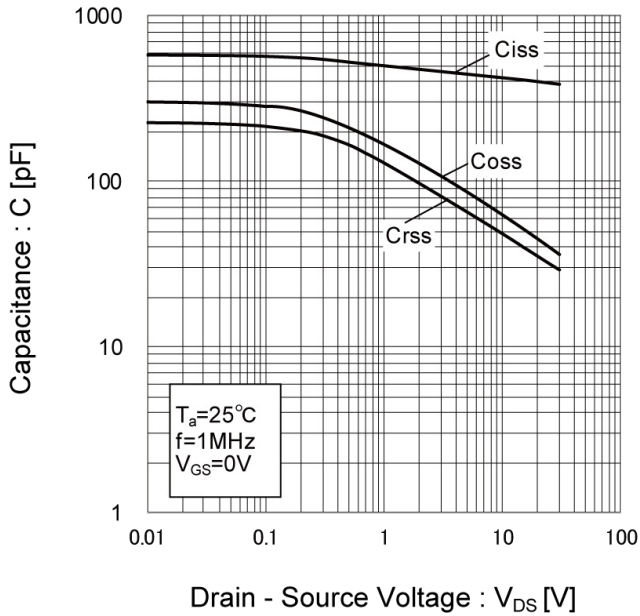


Fig.18 Switching Characteristics

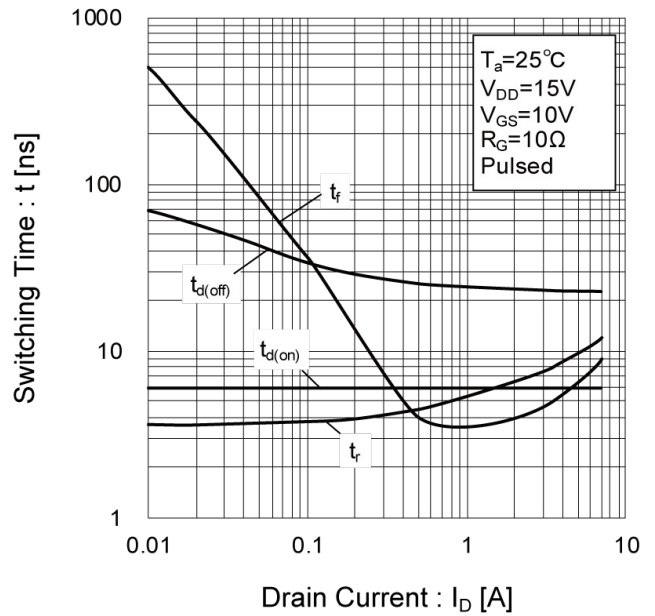


Fig.19 Dynamic Input Characteristics

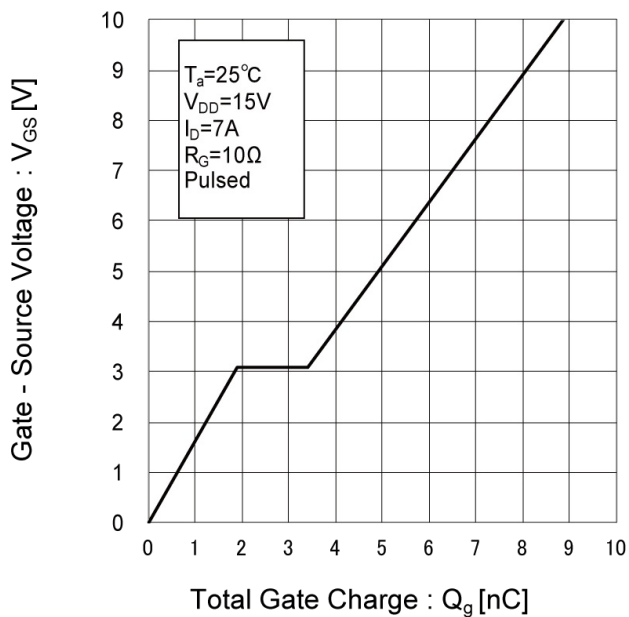
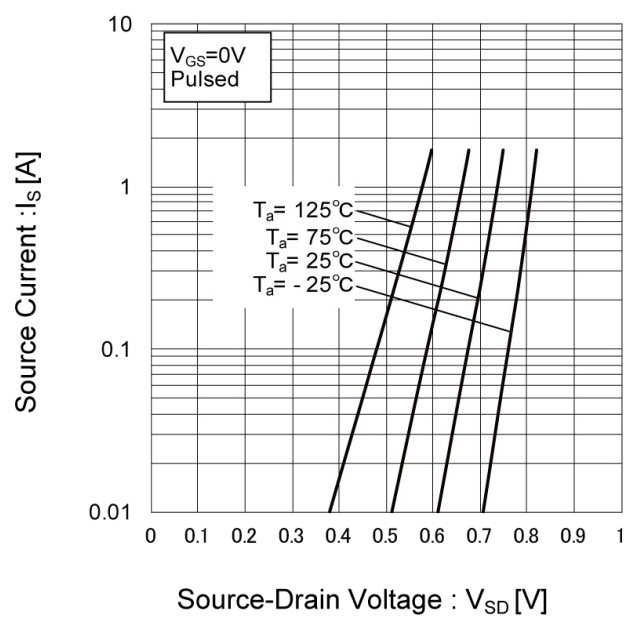


Fig.20 Source Current vs. Source Drain Voltage



● Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

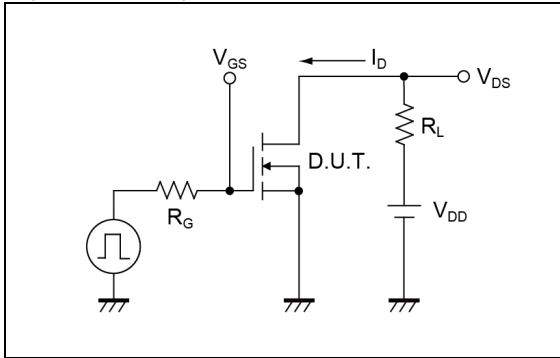


Fig.1-2 Switching Waveforms

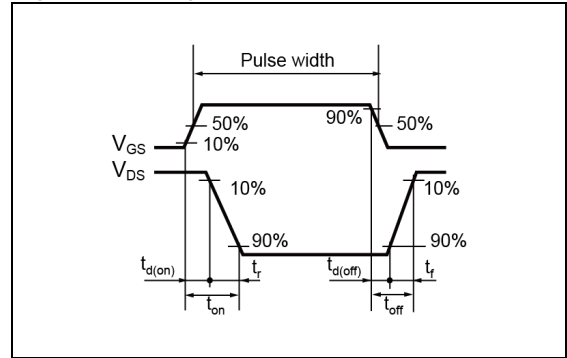


Fig.2-1 Gate Charge Measurement Circuit

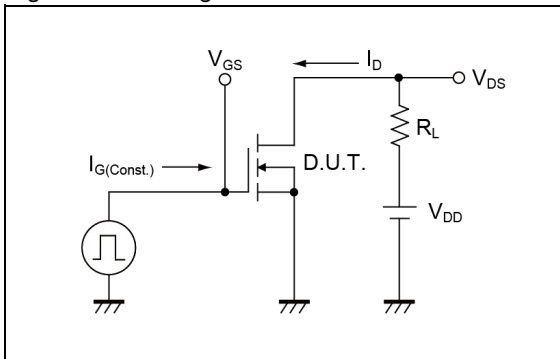
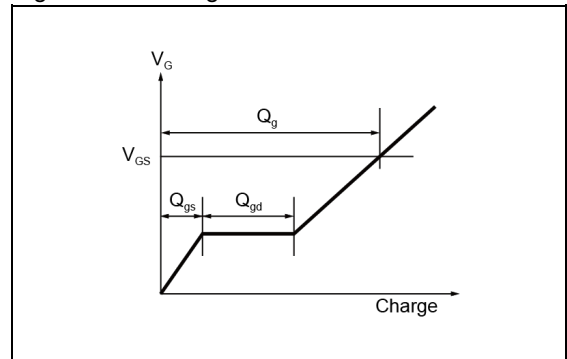


Fig.2-2 Gate Charge Waveform

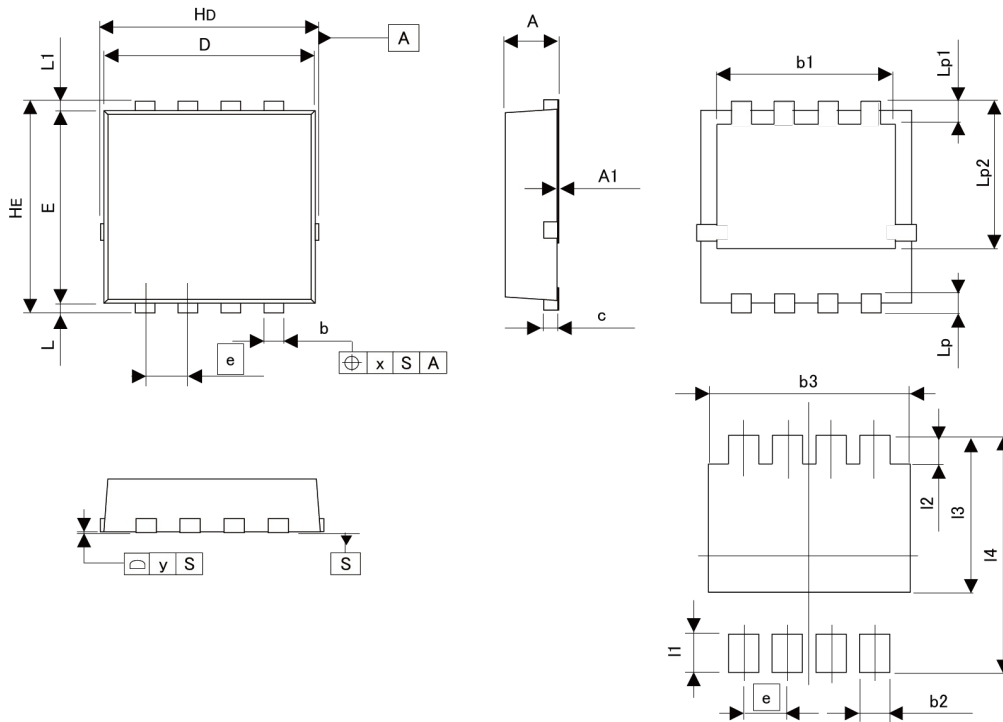


● Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

●Dimensions

HSMT8



Pattern of terminal position areas  
[Not a recommended pattern of soldering pads]

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.70	0.90	0.028	0.035
A1	0.00	0.05	0.000	0.002
b	0.27	0.37	0.011	0.015
b1	2.50	2.70	0.098	0.106
c	0.10	0.30	0.004	0.012
D	3.10	3.30	0.122	0.130
E	2.90	3.10	0.114	0.122
e	0.65		0.026	
Hd	3.20	3.40	0.126	0.134
HE	3.20	3.40	0.126	0.134
L	0.07	0.25	0.003	0.010
L1	0.07	0.25	0.003	0.010
Lp	0.20	0.40	0.008	0.016
Lp1	0.25	0.45	0.010	0.018
Lp2	2.20	2.40	0.087	0.094
x	-	0.10	-	0.004
y	-	0.10	-	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	-	0.47	-	0.019
b3	-	2.70	-	0.106
I1	-	0.50	-	0.020
I2	-	0.55	-	0.022
I3	-	2.40	-	0.094
I4	-	3.40	-	0.134

Dimension in mm/inches

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